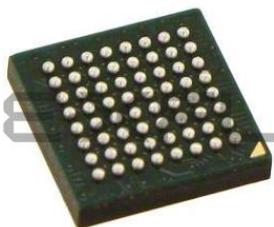


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Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I ² C, IrDA, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	40
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 13x16b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LFBGA
Supplier Device Package	64-MAPBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk20dn64vmp5

Terminology and guidelines

Field	Description	Values
FFF	Program flash memory size	• 32 = 32 KB • 64 = 64 KB • 128 = 128 KB • 256 = 256 KB • 512 = 512 KB • 1M0 = 1 MB
R	Silicon revision	• Z = Initial • (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = -40 to 105 • C = -40 to 85
PP	Package identifier	• FM = 32 QFN (5 mm x 5 mm) • FT = 48 QFN (7 mm x 7 mm) • LF = 48 LQFP (7 mm x 7 mm) • LH = 64 LQFP (10 mm x 10 mm) • MP = 64 MAPBGA (5 mm x 5 mm) • LK = 80 LQFP (12 mm x 12 mm) • MB = 81 MAPBGA (8 mm x 8 mm) • LL = 100 LQFP (14 mm x 14 mm) • ML = 104 MAPBGA (8 mm x 8 mm) • MC = 121 MAPBGA (8 mm x 8 mm) • LQ = 144 LQFP (20 mm x 20 mm) • MD = 144 MAPBGA (13 mm x 13 mm) • MJ = 256 MAPBGA (17 mm x 17 mm)
CC	Maximum CPU frequency (MHz)	• 5 = 50 MHz • 7 = 72 MHz • 10 = 100 MHz • 12 = 120 MHz • 15 = 150 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

2.4 Example

This is an example part number:

MK20DN32VLH5

3 Terminology and guidelines

5.2 Nonswitching electrical specifications

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	V_{DD} -to- V_{DDA} differential voltage	-0.1	0.1	V	
$V_{SS} - V_{SSA}$	V_{SS} -to- V_{SSA} differential voltage	-0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ $1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}$	$0.7 \times V_{DD}$ $0.75 \times V_{DD}$	— —	V V	
V_{IL}	Input low voltage $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ $1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}$	— —	$0.35 \times V_{DD}$ $0.3 \times V_{DD}$	V V	
V_{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I_{ICIO}	I/O pin DC injection current — single pin $V_{IN} < V_{SS}-0.3\text{V}$ (Negative current injection) $V_{IN} > V_{DD}+0.3\text{V}$ (Positive current injection)	-3 —	— +3	mA	1
I_{ICont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins - Negative current injection - Positive current injection	-25 —	— +25	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is greater than V_{AIO_MIN} ($=V_{SS}-0.3\text{V}$) and V_{IN} is less than V_{AIO_MAX} ($=V_{DD}+0.3\text{V}$) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO_MIN}-V_{IN})/|I_{IC}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO_MAX})/|I_{IC}|$. Select the larger of these two calculated resistances.

- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL

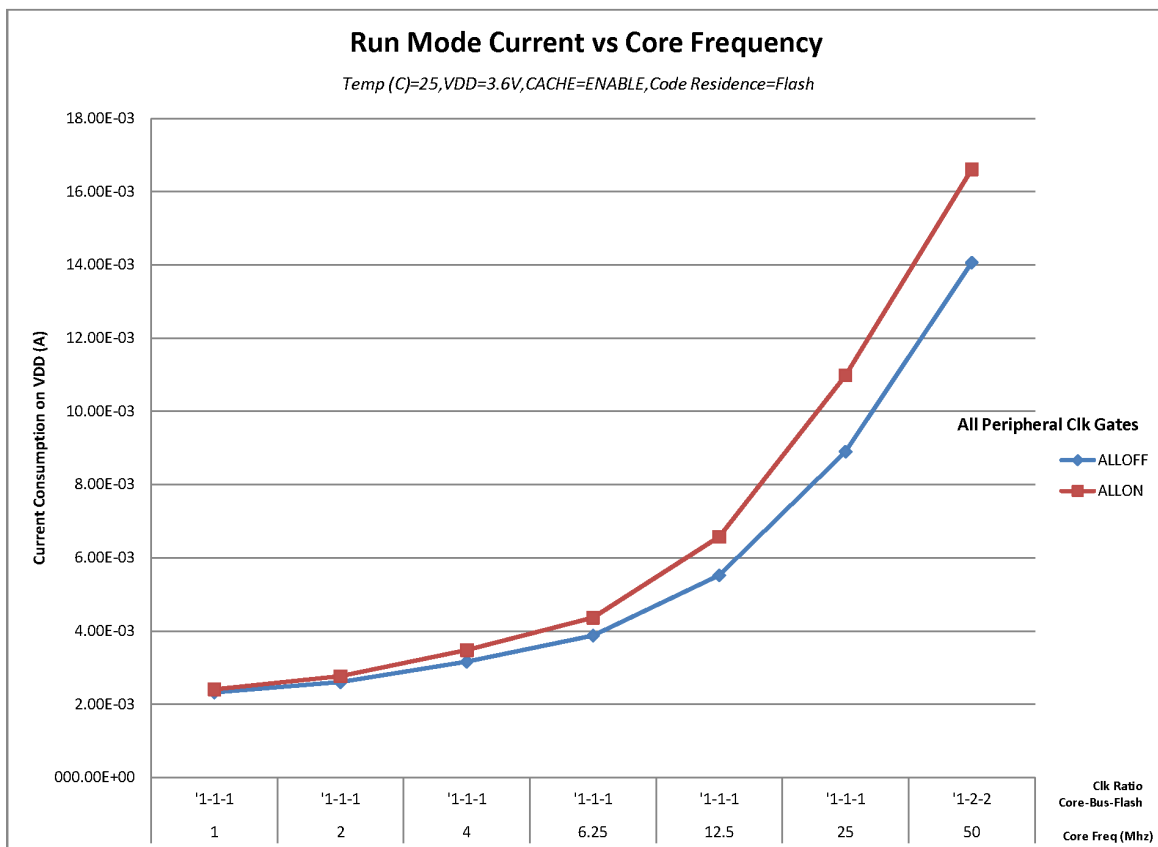


Figure 2. Run mode supply current vs. core frequency

Table 10. General switching specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
	Port rise and fall time (low drive strength)				5
	- Slew disabled $1.71 \leq V_{DD} \leq 2.7V$ $2.7 \leq V_{DD} \leq 3.6V$ - Slew enabled $1.71 \leq V_{DD} \leq 2.7V$ $2.7 \leq V_{DD} \leq 3.6V$	—	12	ns	
		—	6	ns	
		—	36	ns	
		—	24	ns	

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
2. The greater synchronous and asynchronous timing must be met.
3. This is the minimum pulse width that is guaranteed to be recognized as a pin interrupt request in Stop, VLPS, LLS, and VLLSx modes.
4. 75pF load
5. 15pF load

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	−40	125	°C
T_A	Ambient temperature	−40	105	°C

5.4.2 Thermal attributes

Board type	Symbol	Description	64 MAPBGA	64 LQFP	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	107	65	°C/W	1, 2
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	56	46	°C/W	1, 3

Table continues on the next page...

Table 14. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I _{DDOSC}	Supply current — high gain mode (HGO=1)					1
	• 32 kHz	—	25	—	μA	
	• 4 MHz	—	400	—	μA	
	• 8 MHz (RANGE=01)	—	500	—	μA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C _x	EXTAL load capacitance	—	—	—		2, 3
C _y	XTAL load capacitance	—	—	—		2, 3
R _F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R _S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V _{pp} ⁵	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V _{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V _{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C

2. See crystal or resonator manufacturer's recommendation

3. C_x, C_y can be provided by using either the integrated capacitors or by using external components.4. When low power mode is selected, R_F is integrated and must not be attached externally.

Table 16. 32kHz oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
C_{para}	Parasitical capacitance of EXTAL32 and XTAL32	—	5	7	pF
V_{pp} ¹	Peak-to-peak amplitude of oscillation	—	0.6	—	V

1. When a crystal is being used with the 32 kHz oscillator, the EXTAL32 and XTAL32 pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.3.2 32kHz oscillator frequency specifications

Table 17. 32kHz oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal	—	32.768	—	kHz	
t_{start}	Crystal start-up time	—	1000	—	ms	1
$f_{ec_extal32}$	Externally provided input clock frequency	—	32.768	—	kHz	2
$V_{ec_extal32}$	Externally provided input clock amplitude	700	—	V_{BAT}	mV	2, 3

1. Proper PC board layout procedures must be followed to achieve specifications.
2. This specification is for an externally supplied clock driven to EXTAL32 and does not apply to any other clock input. The oscillator remains enabled and XTAL32 must be left unconnected.
3. The parameter specified is a peak-to-peak value and V_{IH} and V_{IL} specifications do not apply. The voltage of the applied clock must be within the range of V_{SS} to V_{BAT} .

6.4 Memories and memory interfaces

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

6.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 18. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{hvp gm4}$	Longword Program high-voltage time	—	7.5	18	μs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversblk32k}$	Erase Block high-voltage time for 32 KB	—	52	452	ms	1
$t_{hversblk128k}$	Erase Block high-voltage time for 128 KB	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands

Table 19. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1blk32k}$	Read 1s Block execution time	—	—	0.5	ms	
$t_{rd1blk128k}$	32 KB data flash 128 KB program flash	—	—	1.7	ms	
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	
$t_{ersblk32k}$	Erase Flash Block execution time	—	55	465	ms	2
$t_{ersblk128k}$	32 KB data flash 128 KB program flash	—	61	495	ms	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
$t_{pgmsec512}$	Program Section execution time	—	4.7	—	ms	
$t_{pgmsec1k}$	512 B flash 1 KB flash	—	9.3	—	ms	
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	
t_{ersall}	Erase All Blocks execution time	—	115	1000	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1
$t_{pgmpart32k}$	Program Partition for EEPROM execution time	—	70	—	ms	
$t_{setramff}$	Set FlexRAM Function execution time:	—	50	—	μs	
$t_{setram8k}$	- Control Code 0xFF 8 KB EEPROM backup	—	0.3	0.5	ms	
$t_{setram32k}$	32 KB EEPROM backup	—	0.7	1.0	ms	
Byte-write to FlexRAM for EEPROM operation						
$t_{eewr8bers}$	Byte-write to erased FlexRAM location execution time	—	175	260	μs	3
$t_{eewr8b8k}$	Byte-write to FlexRAM execution time:	—	340	1700	μs	
$t_{eewr8b16k}$	8 KB EEPROM backup 16 KB EEPROM backup	—	385	1800	μs	
$t_{eewr8b32k}$	32 KB EEPROM backup	—	475	2000	μs	

Table continues on the next page...

Table 19. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
Word-write to FlexRAM for EEPROM operation						
$t_{\text{eewr16bers}}$	Word-write to erased FlexRAM location execution time	—	175	260	μs	
$t_{\text{eewr16b8k}}$	Word-write to FlexRAM execution time: • 8 KB EEPROM backup	—	340	1700	μs	
$t_{\text{eewr16b16k}}$	• 16 KB EEPROM backup	—	385	1800	μs	
$t_{\text{eewr16b32k}}$	• 32 KB EEPROM backup	—	475	2000	μs	
Longword-write to FlexRAM for EEPROM operation						
$t_{\text{eewr32bers}}$	Longword-write to erased FlexRAM location execution time	—	360	540	μs	
$t_{\text{eewr32b8k}}$	Longword-write to FlexRAM execution time: • 8 KB EEPROM backup	—	545	1950	μs	
$t_{\text{eewr32b16k}}$	• 16 KB EEPROM backup	—	630	2050	μs	
$t_{\text{eewr32b32k}}$	• 32 KB EEPROM backup	—	810	2250	μs	

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

6.4.1.3 Flash high voltage current behaviors

Table 20. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
$I_{\text{DD_PGM}}$	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
$I_{\text{DD_ERS}}$	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications

Table 21. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						
$t_{\text{nvmretp10k}}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{\text{nvmretp1k}}$	Data retention after up to 1 K cycles	20	100	—	years	
n_{nvmcycp}	Cycling endurance	10 K	50 K	—	cycles	2
Data Flash						
$t_{\text{nvmretd10k}}$	Data retention after up to 10 K cycles	5	50	—	years	

Table continues on the next page...

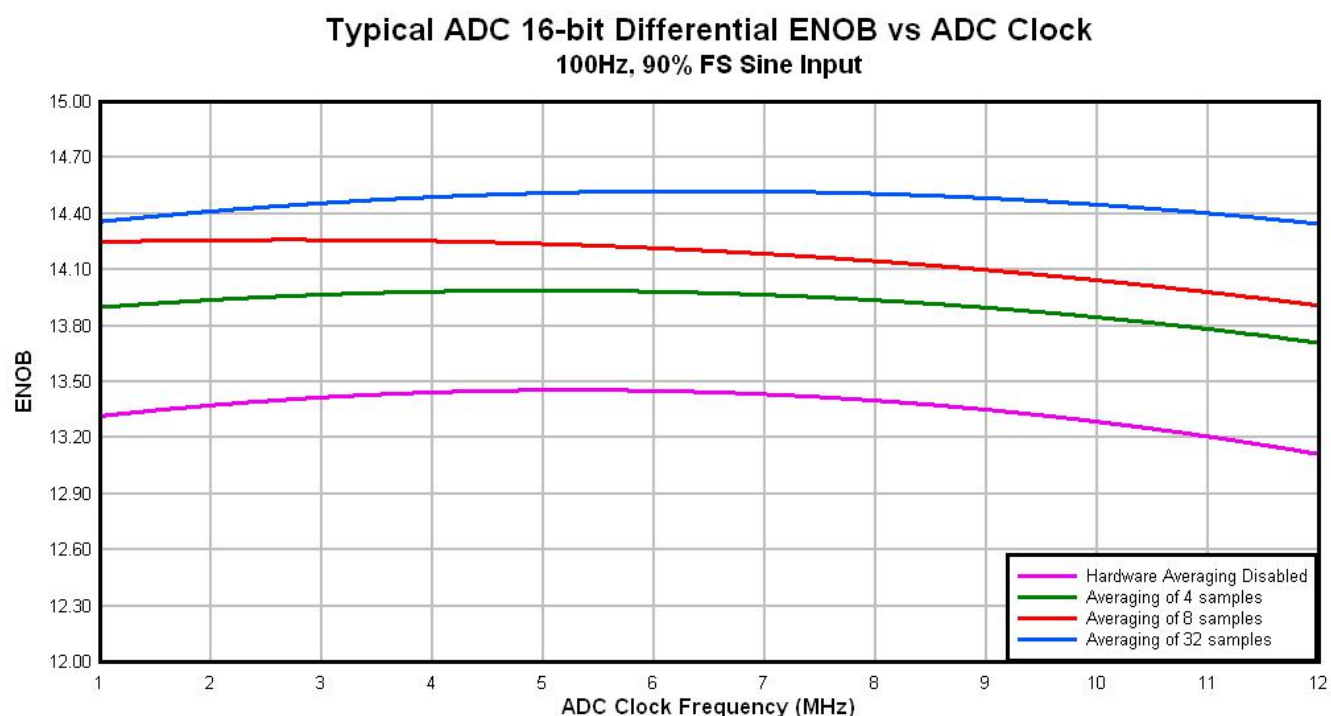


Figure 11. Typical ENOB vs. ADC_CLK for 16-bit differential mode

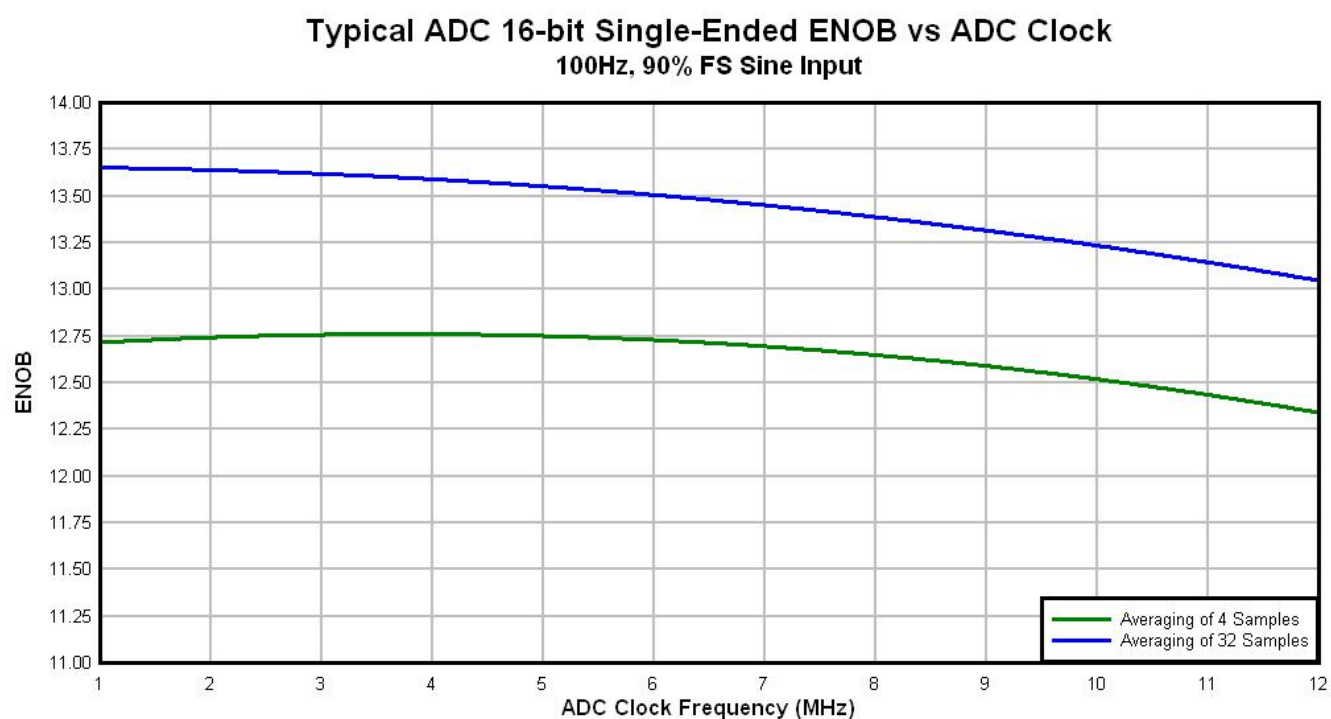


Figure 12. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

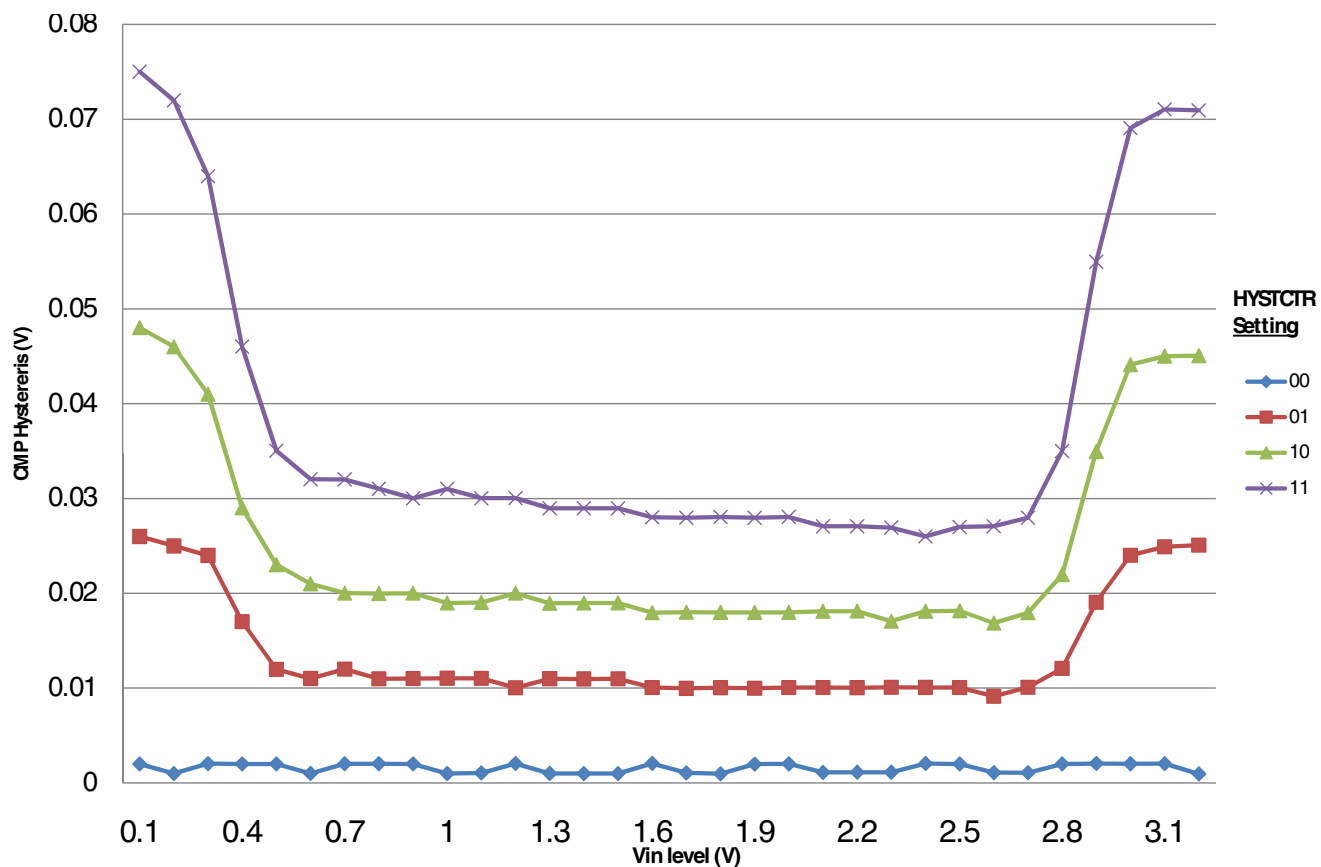


Figure 13. Typical hysteresis vs. Vin level (VDD=3.3V, PMODE=0)

6.8.1 USB electrical specifications

The USB electricals for the USB On-the-Go module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit <http://www.usb.org>.

6.8.2 USB DCD electrical specifications

Table 30. USB DCD electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V _{DP_SRC}	USB_DP source voltage (up to 250 μ A)	0.5	—	0.7	V
V _{LGC}	Threshold voltage for logic high	0.8	—	2.0	V
I _{DP_SRC}	USB_DP source current	7	10	13	μ A
I _{DM_SINK}	USB_DM sink current	50	100	150	μ A
R _{DM_DWN}	D- pulldown resistance for data pin contact detect	14.25	—	24.8	k Ω
V _{DAT_REF}	Data detect voltage	0.25	0.33	0.4	V

6.8.3 USB VREG electrical specifications

Table 31. USB VREG electrical specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
V _{REGIN}	Input supply voltage	2.7	—	5.5	V	
I _{DDon}	Quiescent current — Run mode, load current equal zero, input supply (V _{REGIN}) > 3.6 V	—	120	186	μ A	
I _{DDstby}	Quiescent current — Standby mode, load current equal zero	—	1.1	1.54	μ A	
I _{DDoff}	Quiescent current — Shutdown mode - V_{REGIN} = 5.0 V and temperature=25C - Across operating voltage and temperature	—	650	—	nA	
		—	—	4	μ A	
I _{LOADrun}	Maximum load current — Run mode	—	—	120	mA	
I _{LOADstby}	Maximum load current — Standby mode	—	—	1	mA	
V _{Reg33out}	Regulator output voltage — Input supply (V _{REGIN}) > 3.6 V - Run mode - Standby mode	3	3.3	3.6	V	
		2.1	2.8	3.6	V	
V _{Reg33out}	Regulator output voltage — Input supply (V _{REGIN}) < 3.6 V, pass-through mode	2.1	—	3.6	V	2

Table continues on the next page...

**Table 31. USB VREG electrical specifications
(continued)**

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
C _{OUT}	External output capacitor	1.76	2.2	8.16	μF	
ESR	External output capacitor equivalent series resistance	1	—	100	mΩ	
I _{LIM}	Short circuit current	—	290	—	mA	

1. Typical values assume VREGIN = 5.0 V, Temp = 25 °C unless otherwise stated.

2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to I_{Load}.

6.8.4 DSPI switching specifications (limited voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 32. Master mode DSPI timing (limited voltage range)

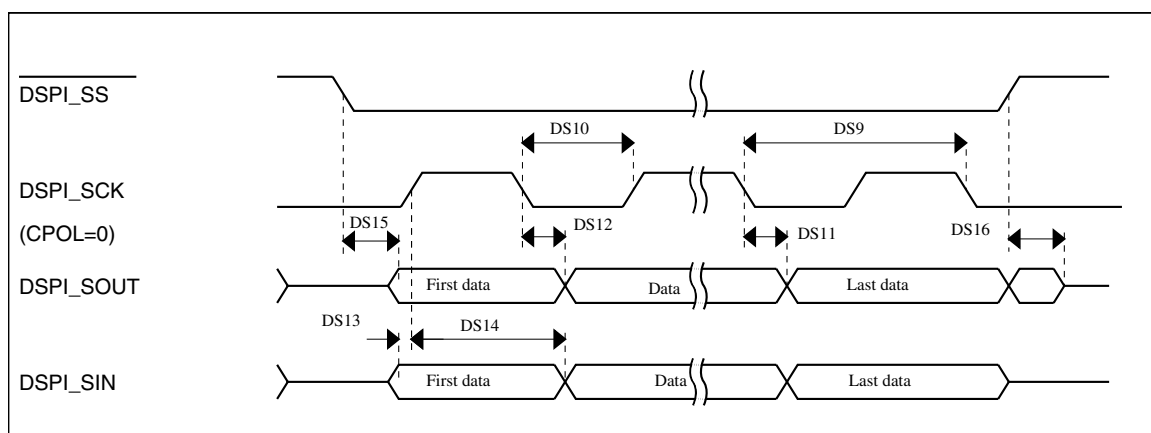
Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	25	MHz	
DS1	DSPI_SCK output cycle time	2 x t _{BUS}	—	ns	
DS2	DSPI_SCK output high/low time	(t _{SCK} /2) – 2	(t _{SCK} /2) + 2	ns	
DS3	DSPI_PCS _n valid to DSPI_SCK delay	(t _{BUS} x 2) – 2	—	ns	1
DS4	DSPI_SCK to DSPI_PCS _n invalid delay	(t _{BUS} x 2) – 2	—	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	—	8	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	0	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	14	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].

2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

Table 35. Slave mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	—	6.25	MHz
DS9	DSPI_SCK input cycle time	$8 \times t_{\text{BUS}}$	—	ns
DS10	DSPI_SCK input high/low time	$(t_{\text{SCK}/2}) - 4$	$(t_{\text{SCK}/2}) + 4$	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	24	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	3.2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI_SS}}$ active to DSPI_SOUT driven	—	19	ns
DS16	$\overline{\text{DSPI_SS}}$ inactive to DSPI_SOUT not driven	—	19	ns

**Figure 18. DSPI classic SPI timing — slave mode**

6.8.6 I²C switching specifications

See [General switching specifications](#).

6.8.7 UART switching specifications

See [General switching specifications](#).

6.8.8 I2S/SAI Switching Specifications

This section provides the AC timing for the I2S/SAI module in master mode (clocks are driven) and slave mode (clocks are input). All timing is given for noninverted serial clock polarity (TCR2[BCP] is 0, RCR2[BCP] is 0) and a noninverted frame sync (TCR4[FSP] is 0, RCR4[FSP] is 0). If the polarity of the clock and/or the frame sync have been inverted, all the timing remains valid by inverting the bit clock signal (BCLK) and/or the frame sync (FS) signal shown in the following figures.

6.8.8.1 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Table 36. I2S/SAI master mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	25	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

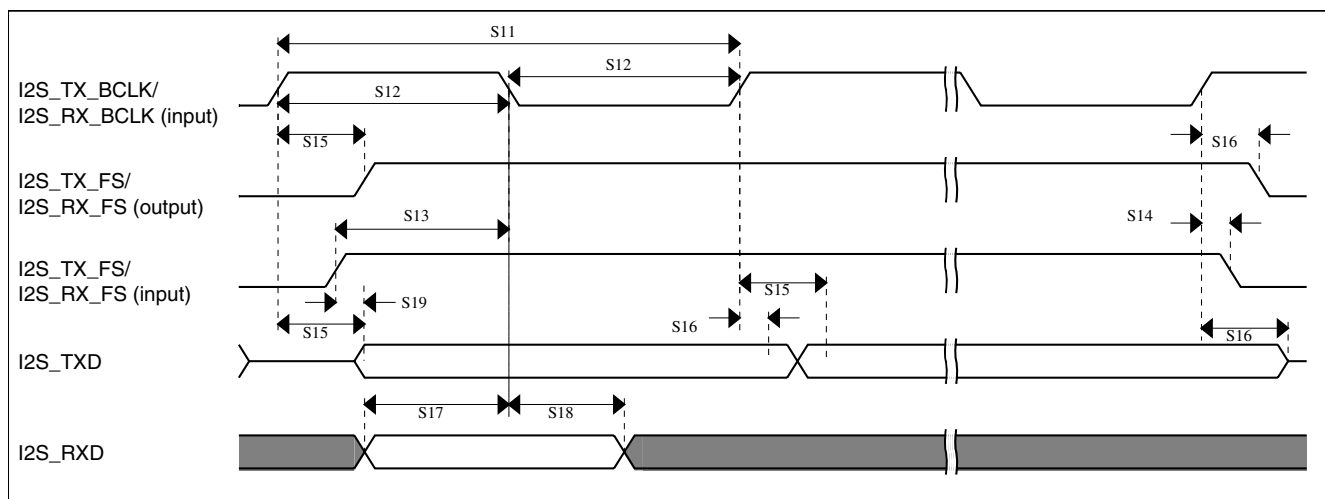


Figure 20. I2S/SAI timing — slave modes

6.8.8.2 VLPR, VLPW, and VLPS mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in VLPR, VLPW, and VLPS modes.

Table 38. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	62.5	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	250	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	45	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	45	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	45	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

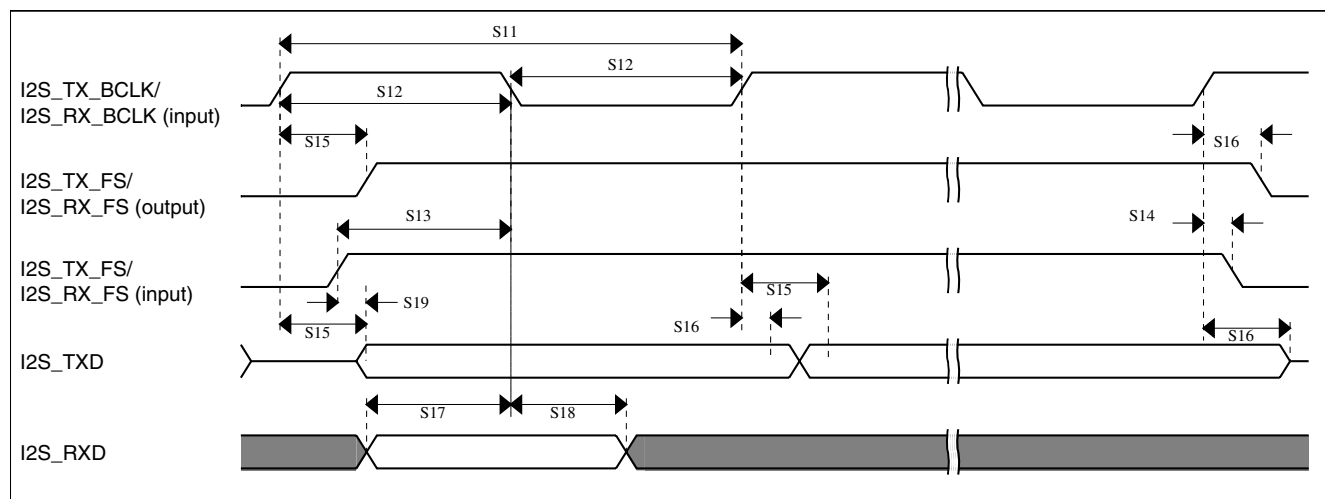


Figure 22. I2S/SAI timing — slave modes

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 40. TSI electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DDTSI}	Operating voltage	1.71	—	3.6	V	
C_{ELE}	Target electrode capacitance range	1	20	500	pF	1
f_{REFmax}	Reference oscillator frequency	—	8	15	MHz	2, 3
f_{ELEmax}	Electrode oscillator frequency	—	1	1.8	MHz	2, 4
C_{REF}	Internal reference capacitor	—	1	—	pF	
V_{DELTA}	Oscillator delta voltage	—	500	—	mV	2, 5
I_{REF}	Reference oscillator current source base current 2 μA setting (REFCHRG = 0) 32 μA setting (REFCHRG = 15)	— —	2 36	3 50	μ A	2, 6
I_{ELE}	Electrode oscillator current source base current 2 μA setting (EXTCHRG = 0) 32 μA setting (EXTCHRG = 15)	— —	2 36	3 50	μ A	2, 7
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	8
Pres20	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	9
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	10
MaxSens	Maximum sensitivity	0.008	1.46	—	fF/count	11
Res	Resolution	—	—	16	bits	

Table continues on the next page...

8 Pinout

8.1 K20 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

64 MAP BGA	64 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
A1	1	PTE0	DISABLED		PTE0		UART1_TX				RTC_CLKOUT	
B1	2	PTE1/ LLWU_P0	DISABLED		PTE1/ LLWU_P0		UART1_RX					
C5	3	VDD	VDD	VDD								
C4	4	VSS	VSS	VSS								
E1	5	USB0_DP	USB0_DP	USB0_DP								
D1	6	USB0_DM	USB0_DM	USB0_DM								
E2	7	VOUT33	VOUT33	VOUT33								
D2	8	VREGIN	VREGIN	VREGIN								
G1	9	ADC0_DP0	ADC0_DP0	ADC0_DP0								
F1	10	ADC0_DM0	ADC0_DM0	ADC0_DM0								
G2	11	ADC0_DP3	ADC0_DP3	ADC0_DP3								
F2	12	ADC0_DM3	ADC0_DM3	ADC0_DM3								
F4	13	VDDA	VDDA	VDDA								
G4	14	VREFH	VREFH	VREFH								
G3	15	VREFL	VREFL	VREFL								
F3	16	VSSA	VSSA	VSSA								
H1	17	VREF_OUT/ CMP1_IN5/ CMP0_IN5	VREF_OUT/ CMP1_IN5/ CMP0_IN5	VREF_OUT/ CMP1_IN5/ CMP0_IN5								
H2	18	CMP1_IN3/ ADC0_SE23	CMP1_IN3/ ADC0_SE23	CMP1_IN3/ ADC0_SE23								
H3	19	XTAL32	XTAL32	XTAL32								
H4	20	EXTAL32	EXTAL32	EXTAL32								
H5	21	VBAT	VBAT	VBAT								
D3	22	PTA0	JTAG_TCLK/ SWD_CLK/ EZP_CLK	TSIO_CH1	PTA0	UART0_CTS_ b/ UART0_COL_ b	FTM0_CH5				JTAG_TCLK/ SWD_CLK	EZP_CLK
D4	23	PTA1	JTAG_TDI/ EZP_DI	TSIO_CH2	PTA1	UART0_RX	FTM0_CH6				JTAG_TDI	EZP_DI

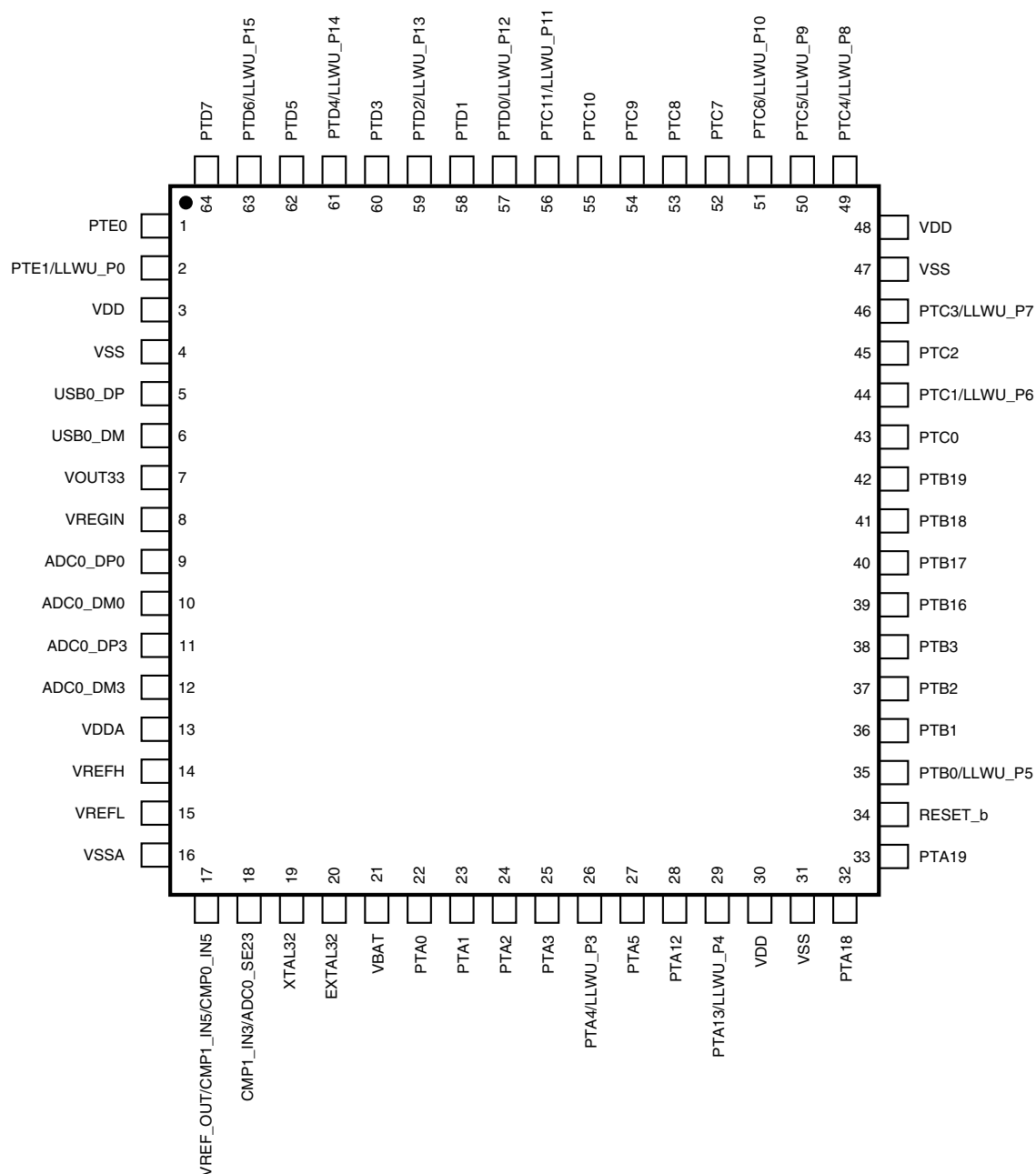


Figure 23. K20 64 LQFP Pinout Diagram

	1	2	3	4	5	6	7	8	
A	PTE0	PTD7	PTD4/ LLWU_P14	PTD1	PTC11/ LLWU_P11	PTC8	PTC6/ LLWU_P10	PTC5/ LLWU_P9	A
B	PTE1/ LLWU_P0	PTD6/ LLWU_P15	PTD3	PTC10	PTC9	PTC7	PTC2	PTC4/ LLWU_P8	B
C	PTD5	PTD2/ LLWU_P13	PTD0/ LLWU_P12	VSS	VDD	PTC1/ LLWU_P6	PTB19	PTC3/ LLWU_P7	C
D	USB0_DM	VREGIN	PTA0	PTA1	PTA3	PTB18	PTB17	PTC0	D
E	USB0_DP	VOOUT33	VSS	VDD	PTA2	PTB16	PTB2	PTB3	E
F	ADC0_DM0	ADC0_DM3	VSSA	VDDA	PTA5	PTB1	PTB0/ LLWU_P5	RESET_b	F
G	ADC0_DP0	ADC0_DP3	VREFL	VREFH	PTA4/ LLWU_P3	PTA13/ LLWU_P4	VDD	PTA19	G
H	VREF_OUT, CMP1_IN5/ ADC0_IN5	CMP1_IN3/ ADC0_SE23	XTAL32	EXTAL32	VBAT	PTA12	VSS	PTA18	H
	1	2	3	4	5	6	7	8	

Figure 24. K20 64 MAPBGA Pinout Diagram

9 Revision History

The following table provides a revision history for this document.

Table 41. Revision History

Rev. No.	Date	Substantial Changes
2	2/2012	Initial public release
3	4/2012	- Replaced TBDs throughout. - Updated "Power mode transition operating behaviors" table. - Updated "Power consumption operating behaviors" table. - For "Diagram: Typical IDD_RUN operating behavior" section, added "VLPR mode supply current vs. core frequency" figure. - Updated "EMC radiated emissions operating behaviors" section. - Updated "Thermal operating requirements" section. - Updated "MCG specifications" table. - Updated "VREF full-range operating behaviors" table. - Updated "I2S/SAI Switching Specifications" section. - Updated "TSI electrical specifications" table.

Table continues on the next page...

Table 41. Revision History (continued)

Rev. No.	Date	Substantial Changes
4	5/2012	- For the "32kHz oscillator frequency specifications", added specifications for an externally driven clock. - Renamed section "Flash current and power specifications" to section "Flash high voltage current behaviors" and improved the specifications. - For the "VREF full-range operating behaviors" table, removed the Ac (aging coefficient) specification. - Corrected the following DSPI switching specifications: tightened DS5, DS6, and DS7; relaxed DS11 and DS13. - For the "TSI electrical specifications", changed and clarified the example calculations for the MaxSens specification.